

# 2048Kx8 Nonvolatile SRAM

#### **Features**

- ➤ Data retention in the absence of power
- ➤ Automatic write-protection during power-up/power-down cycles
- ➤ Conventional SRAM operation; unlimited write cycles
- ➤ 5-year minimum data retention in absence of power
- ➤ Battery internally isolated until power is applied

### **General Description**

The CMOS bq4017 is a nonvolatile 16,777,216-bit static RAM organized as 2,097,152 words by 8 bits. The integral control circuitry and lithium energy source provide reliable nonvolatility coupled with the unlimited write cycles of standard SRAM.

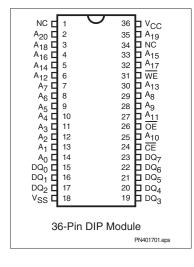
The control circuitry constantly monitors the single 5V supply for an out-of-tolerance condition. When  $V_{\rm CC}$  falls out of tolerance, the SRAM is unconditionally write-protected to prevent an inadvertent write operation.

At this time the integral energy source is switched on to sustain the memory until after  $V_{\rm CC}$  returns valid.

The bq4017 uses extremely low standby current CMOS SRAMs, coupled with small lithium coin cells to provide nonvolatility without long write-cycle times and the write-cycle limitations associated with EE-PROM

The bq4017 has the same interface as industry-standard SRAMs and requires no external circuitry.

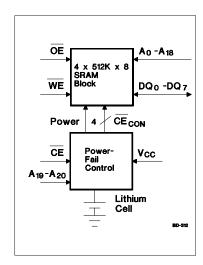
### **Pin Connections**



### **Pin Names**

$A_0 - A_{20}$	Address inputs
DQ <sub>0</sub> –DQ <sub>7</sub>	Data input/output
CE	Chip enable input
ŌĒ	Output enable input
$\overline{\mathrm{WE}}$	Write enable input
$V_{CC}$	Supply voltage input
$V_{SS}$	Ground
NC	No connect

### **Block Diagram**



#### **Selection Guide**

Part Number	Maximum Access Time (ns)	Negative Supply Tolerance	Part Number	Maximum Access Time (ns)	Negative Supply Tolerance
bq4017MC -70	70	-5%	bq4017YMC -70	70	-10%

### **Functional Description**

When power is valid, the bq4017 operates as a standard CMOS SRAM. During power-down and power-up cycles, the bq4017 acts as a nonvolatile memory, automatically protecting and preserving the memory contents.

Power-down/power-up control circuitry constantly monitors the  $V_{\rm CC}$  supply for a power-fail-detect threshold  $V_{\rm PFD}$ . The bq4017 monitors for  $V_{\rm PFD}=4.62V$  typical for use in systems with 5% supply tolerance. The bq4017Y monitors for  $V_{\rm PFD}=4.37V$  typical for use in systems with 10% supply tolerance.

When V<sub>CC</sub> falls below the V<sub>PFD</sub> threshold, the SRAM automatically write-protects the data. All outputs become high impedance, and all inputs are treated as "don't care." If a valid access is in process at the time of power-fail detection, the memory cycle continues to completion. If the memory cycle fails to terminate within time twpt, write-protection takes place.

As  $V_{\rm CC}$  falls past  $V_{\rm PFD}$  and approaches 3V, the control circuitry switches to the internal lithium backup supply, which provides data retention until valid  $V_{\rm CC}$  is applied.

When  $V_{\rm CC}$  returns to a level above the internal backup cell voltage, the supply is switched back to  $V_{\rm CC}$ . After  $V_{\rm CC}$  ramps above the  $V_{\rm PFD}$  threshold, write-protection continues for a time  $t_{\rm CER}$  (120ms maximum) to allow for processor stabilization. Normal memory operation may resume after this time.

The internal coin cells used by the bq4017 have an extremely long shelf life. The bq4017 provides data retention for more than 5 years in the absence of system power.

As shipped from Unitrode, the integral lithium cells are electrically isolated from the memory. (Self-discharge in this condition is approximately 0.5% per year.) Following the first application of  $V_{\rm CC}$ , this isolation is broken, and the lithium backup provides data retention on subsequent power-downs.

#### **Truth Table**

Mode	CE	WE	ŌĒ	I/O Operation	Power
Not selected	Н	X	X	High Z	Standby
Output disable	L	Н	Н	High Z	Active
Read	L	Н	L	D <sub>OUT</sub>	Active
Write	L	L	X	D <sub>IN</sub>	Active

#### **Absolute Maximum Ratings**

Symbol	Parameter	Value	Unit	Conditions
$V_{\rm CC}$	DC voltage applied on $V_{\rm CC}$ relative to $V_{\rm SS}$	-0.3 to 7.0	V	
$V_{\mathrm{T}}$	DC voltage applied on any pin excluding $V_{\rm CC}$ relative to $V_{\rm SS}$	-0.3 to 7.0	V	$V_T \leq V_{CC} + 0.3$
Topr	Operating temperature	0 to +70	°C	
T <sub>STG</sub>	Storage temperature	-40 to +70	°C	
$T_{ m BIAS}$	Temperature under bias	-10 to +70	°C	
$T_{SOLDER}$	Soldering temperature	+260	°C	For 10 seconds

Note:

Permanent device damage may occur if **Absolute Maximum Ratings** are exceeded. Functional operation should be limited to the Recommended DC Operating Conditions detailed in this data sheet. Exposure to conditions beyond the operational limits for extended periods of time may affect device reliability.

# Not Recommended for new Designs

# bq4017/bq4017Y

## Recommended DC Operating Conditions (T<sub>A</sub> = 0 to 70°C)

Symbol	Parameter	Minimum	Typical	Maximum	Unit	Notes
77	V <sub>CC</sub> Supply voltage	4.5	5.0	5.5	V	bq4017Y
VCC		4.75	5.0	5.5	V	bq4017
$V_{\rm SS}$	Supply voltage	0	0	0	V	
$V_{ m IL}$	Input low voltage	-0.3	-	0.8	V	
$V_{\mathrm{IH}}$	Input high voltage	2.2	-	$V_{CC} + 0.3$	V	

Note: Typical values indicate operation at  $T_A = 25$ °C.

### DC Electrical Characteristics (TA = 0 to 70°C, VCCmin ≤ VCC ≤ VCCmax)

Symbol	Parameter	Minimum	Typical	Maximum	Unit	Conditions/Notes
$I_{LI}$	Input leakage current	-	-	± 4	μΑ	$V_{\rm IN}$ = $V_{\rm SS}$ to $V_{\rm CC}$
$I_{LO}$	Output leakage current	-	-	± 4	μΑ	$\label{eq:center_of_continuous} \begin{array}{l} \overline{CE} = V_{IH} \ or \ \overline{OE} = V_{IH} \ or \\ \overline{WE} = V_{IL} \end{array}$
V <sub>OH</sub>	Output high voltage	2.4	-	-	V	I <sub>OH</sub> = -1.0 mA
$V_{\mathrm{OL}}$	Output low voltage	-	-	0.4	V	$I_{\rm OL}$ = 2.1 mA
I <sub>SB1</sub>	Standby supply current	-	7	17	mA	$\overline{\mathrm{CE}} = \mathrm{V_{IH}}$
$I_{\mathrm{SB2}}$	Standby supply current	-	2.5	5	mA	$\begin{aligned} & \frac{0V}{CE} \leq V_{IN} \leq 0.2V, \\ & \frac{0}{CE} \geq V_{CC} - 0.2V, \\ & \text{or } V_{IN} \geq V_{CC} - 0.2 \end{aligned}$
$I_{CC}$	Operating supply current	-	75	115	mA	$\begin{array}{l} \underline{Min.} \; cycle, duty = 100\%, \\ \overline{CE} = V_{IL} \; , \! I_{I/O} = 0mA, \\ A19 < V_{IL} \; or \; A19 > V_{IH}, \\ A20 < V_{IL} \; or \; A20 > V_{IH} \end{array}$
37	D ( '1 1 4 4 14	4.55	4.62	4.75	V	bq4017
$V_{\mathrm{PFD}}$	Power-fail-detect voltage	4.30	4.37	4.50	V	bq4017Y
$V_{\rm SO}$	Supply switch-over voltage	-	3	-	V	

Note: Typical values indicate operation at  $T_A = 25$ °C,  $V_{CC} = 5V$ .

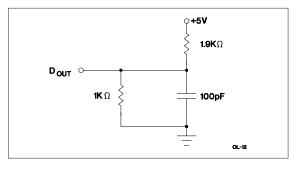
### Capacitance ( $T_A = 25^{\circ}C$ , F = 1MHz, $V_{CC} = 5.0V$ )

Symbol	Parameter	Minimum	Typical	Maximum	Unit	Conditions
C <sub>I/O</sub>	Input/output capacitance	-	-	40	pF	Output voltage = 0V
$C_{IN}$	Input capacitance	-	-	40	pF	Input voltage = 0V

**Note:** These parameters are sampled and not 100% tested.

### **AC Test Conditions**

Parameter	Test Conditions		
Input pulse levels	0V to 3.0V		
Input rise and fall times	5 ns		
Input and output timing reference levels	1.5 V (unless otherwise specified)		
Output load (including scope and jig)	See Figures 1 and 2		



1.9KΩ

1.9KΩ

5pF

out-19

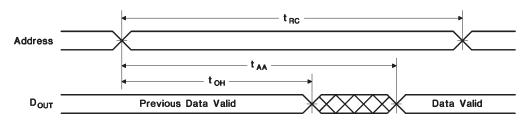
Figure 1. Output Load A

Figure 2. Output Load B

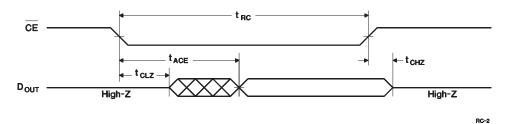
# Read Cycle (TA = 0 to 70°C, $V_{CCmin} \le V_{CC} \le V_{CCmax}$ )

		-7	-70		-70		-70		-70		
Symbol	Parameter	Min.	Max.	Unit	Conditions						
$t_{ m RC}$	Read cycle time	70	-	ns							
$t_{AA}$	Address access time	-	70	ns	Output load A						
$t_{ACE}$	Chip enable access time	-	70	ns	Output load A						
$t_{OE}$	Output enable to output valid	-	35	ns	Output load A						
$t_{CLZ}$	Chip enable to output in low Z	5	-	ns	Output load B						
tolz	Output enable to output in low Z	5	-	ns	Output load B						
$t_{\mathrm{CHZ}}$	Chip disable to output in high Z	0	25	ns	Output load B						
$t_{OHZ}$	Output disable to output in high Z	0	25	ns	Output load B						
toH	Output hold from address change	10	-	ns	Output load A						

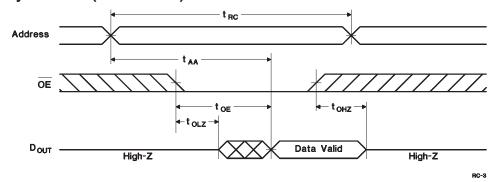
# Read Cycle No. 1 (Address Access)<sup>1,2</sup>



Read Cycle No. 2 (CE Access) 1,3,4



Read Cycle No. 3 (OE Access) 1,5



**Notes:** 

- 1.  $\overline{WE}$  is held high for a read cycle.
- 2. Device is continuously selected:  $\overline{CE}$  =  $\overline{OE}$  =  $V_{IL}$ .
- 3. Address is valid prior to or coincident with  $\overline{\text{CE}}$  transition low.
- $4. \quad \overline{OE} = V_{IL}.$
- 5. Device is continuously selected:  $\overline{\text{CE}} = V_{IL}$ .

# Not Recommended for new Designs

# bq4017/bq4017Y

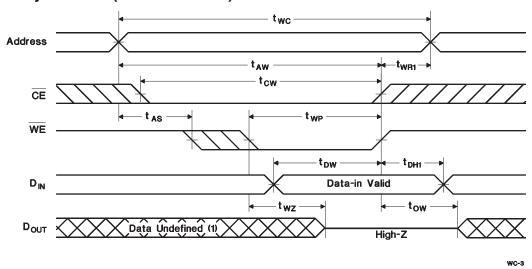
## Write Cycle (TA = 0 to $70^{\circ}$ C, $V_{CCmin} \le V_{CC} \le V_{CCmax}$ )

		-70			
Symbol	Parameter	Min.	Max.	Units	Conditions/Notes
twc	Write cycle time	70	-	ns	
$t_{\mathrm{CW}}$	Chip enable to end of write	65	-	ns	(1)
$t_{AW}$	Address valid to end of write	65	-	ns	(1)
tas	Address setup time	0	-	ns	Measured from address valid to beginning of write. (2)
twp	Write pulse width	55	-	ns	Measured from beginning of write to end of write. (1)
$t_{ m WR1}$	Write recovery time (write cycle 1)	5	-	ns	Measured from $\overline{\text{WE}}$ going high to end of write cycle. (3)
$t_{ m WR2}$	Write recovery time (write cycle 2)	15	-	ns	Measured from $\overline{\text{CE}}$ going high to end of write cycle. (3)
$ m t_{DW}$	Data valid to end of write	30	-	ns	Measured to first low-to-high transition of either $\overline{CE}$ or $\overline{WE}$ .
$ m t_{DH1}$	Data hold time (write cycle 1)	0	-	ns	Measured from $\overline{\text{WE}}$ going high to end of write cycle. (4)
$ m t_{DH2}$	Data hold time (write cycle 2)	10	-	ns	Measured from $\overline{CE}$ going high to end of write cycle. (4)
twz	Write enabled to output in high Z	0	25	ns	I/O pins are in output state. (5)
tow	Output active from end of write	5	-	ns	I/O pins are in output state. (5)

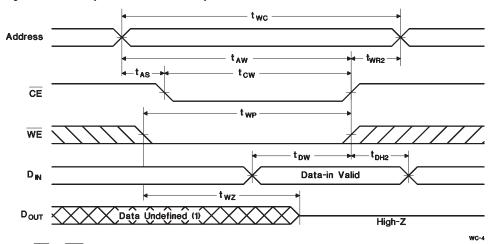
#### **Notes:**

- 1. A write ends at the earlier transition of  $\overline{\text{CE}}$  going high and  $\overline{\text{WE}}$  going high.
- 2. A write occurs during the overlap of a low  $\overline{CE}$  and a low  $\overline{WE}$ . A write begins at the later transition of  $\overline{CE}$  going low and  $\overline{WE}$  going low.
- 3. Either  $t_{WR1}$  or  $t_{WR2}$  must be met.
- 4. Either  $t_{DH1}$  or  $t_{DH2}$  must be met.
- 5. If  $\overline{\text{CE}}$  goes low simultaneously with  $\overline{\text{WE}}$  going low or after  $\overline{\text{WE}}$  going low, the outputs remain in high-impedance state.

# Write Cycle No. 1 (WE-Controlled) $^{1,2,3}$



# Write Cycle No. 2 (CE-Controlled) 1,2,3,4,5



Notes:

- 1.  $\overline{\text{CE}}$  or  $\overline{\text{WE}}$  must be high during address transition.
- 2. Because I/O may be active  $(\overline{OE}\ low)$  during this period, data input signals of opposite polarity to the outputs must not be applied.
- 3. If  $\overline{\text{OE}}$  is high, the I/O pins remain in a state of high impedance.
- 4. Either twR1 or twR2 must be met.
- 5. Either  $t_{\rm DH1}$  or  $t_{\rm DH2}$  must be met.

### Power-Down/Power-Up Cycle (TA = 0 to 70°C)

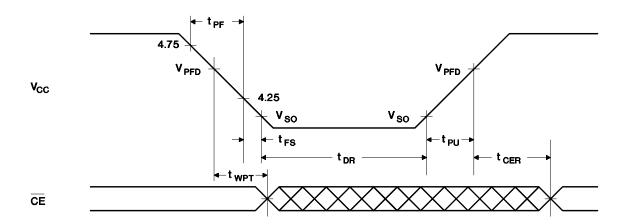
Symbol	Parameter	Minimum	Typical	Maximum	Unit	Conditions
$t_{\mathrm{PF}}$	V <sub>CC</sub> slew, 4.75 to 4.25 V	300	-	-	μs	
$t_{\rm FS}$	$V_{\rm CC}$ slew, 4.25 to $V_{\rm SO}$	10	-	-	μs	
t <sub>PU</sub>	$V_{\rm CC}$ slew, $V_{\rm SO}$ to $V_{\rm PFD}$ (max.)	0	-	-	μs	
t <sub>CER</sub>	Chip enable recovery time	40	80	120	ms	Time during which SRAM is write-protected after V <sub>CC</sub> passes V <sub>FPD</sub> on power-up.
${ m t_{DR}}$	Data-retention time in absence of $V_{\rm CC}$	5	-	-	years	$T_A = 25^{\circ}C. (2)$
twpr	Write-protect time	40	100	150	μs	Delay after $V_{CC}$ slews down past $V_{PFD}$ before SRAM is write-protected.

**Notes:** 

- 1. Typical values indicate operation at  $T_A$  = 25°C,  $V_{\rm CC}$  = 5V.
- 2. Batteries are disconnected from circuit until after  $V_{\rm CC}$  is applied for the first time.  $t_{\rm DR}$  is the accumulated time in absence of power beginning when power is first applied to the device.

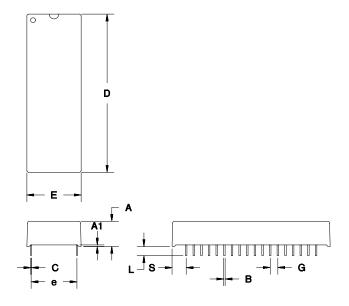
Caution: Negative undershoots below the absolute maximum rating of -0.3V in battery-backup mode may affect data integrity.

## Power-Down/Power-Up Timing



PD-B

# MC: 36-Pin C-Type Module

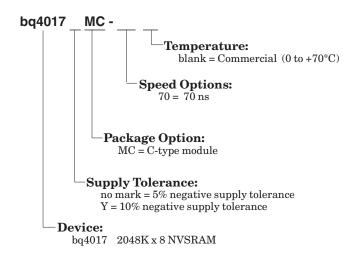


# 36-Pin MC (C-Type Module)

Dimension	Minimum	Maximum
A	0.365	0.375
A1	0.015	-
В	0.017	0.023
C	0.008	0.013
D	2.070	2.100
E	0.710	0.740
e	0.590	0.630
G	0.090	0.110
L	0.120	0.150
S	0.175	0.210

All dimensions are in inches.

# **Ordering Information**





### PACKAGE OPTION ADDENDUM

2-Apr-2011

#### **PACKAGING INFORMATION**

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	Eco Plan <sup>(2)</sup>	Lead/ Ball Finish	MSL Peak Temp <sup>(3)</sup>	Samples (Requires Login)
BQ4017MC-70	NRND	DIP MODULE	MC	36	10	Pb-Free (RoHS)	Call TI	N / A for Pkg Type	
BQ4017YMC-70	NRND	DIP MODULE	MC	36	10	TBD	Call TI	N / A for Pkg Type	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

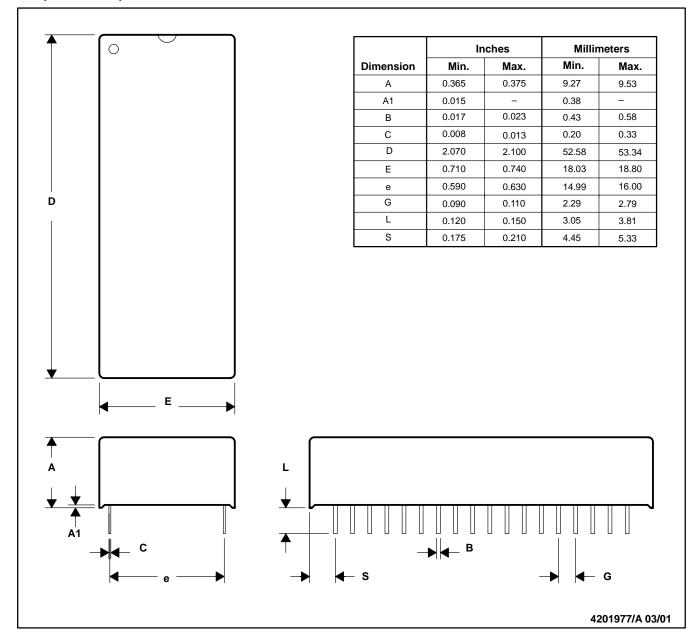
(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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### MC (R-PDIP-T36)

#### PLASTIC DUAL-IN-LINE



NOTES: A. All linear dimensions are in inches (mm).

B. This drawing is subject to change without notice.

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